

SANYO	No.4747	2SJ267
		P-Channel MOS Silicon FET Very High-Speed Switching Applications

Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Surface mount type device making the following possible
 - Reduction in the assembling time for 2SJ267-applied equipment
 - High-density surface mount applications
 - Small size of 2SJ267-applied equipment

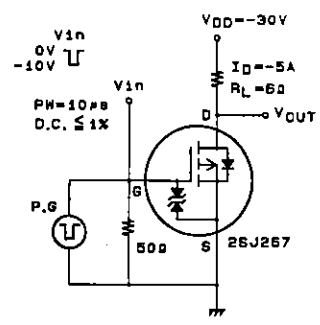
Absolute Maximum Ratings at Ta = 25°C

Drain-to-Source Voltage	V_{DS}		- 60	V
Gate-to-Source Voltage	V_{GS}		± 20	V
Drain Current(DC)	I_D		- 10	A
Drain Current(Pulse)	I_{DP}	$PW \leq 10\mu s, \text{ duty cycle} \leq 1\%$	- 40	A
Allowable Power Dissipation	P_D		1.65	W
		$T_c = 25^\circ C$	60	W
Channel Temperature	T_{ch}		150	°C
Storage Temperature	T_{stg}		- 55 to + 150	°C

Electrical Characteristics at Ta = 25°C

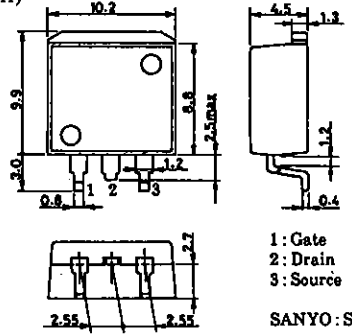
			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1mA, V_{GS} = 0$	- 60			V
G-S Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100\mu A, V_{DS} = 0$	± 20			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60V, V_{GS} = 0$			- 100	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 16V, V_{DS} = 0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10V, I_D = -1mA$	- 1.0		- 2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -5A$	4	7.5		S
Static Drain-to-Source ON-State Resistance	$R_{DS(on)}$	$I_D = -5A, V_{GS} = -10V$		0.11	0.15	Ω
ON-State Resistance	$R_{DS(on)}$	$I_D = -5A, V_{GS} = -4V$		0.15	0.2	Ω
Input Capacitance	C_{iss}	$V_{DS} = -20V, f = 1MHz$		1230		pF
Output Capacitance	C_{oss}	$V_{DS} = -20V, f = 1MHz$		390		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -20V, f = 1MHz$		100		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		16		ns
Rise Time	t_r	∕		40		ns
Turn-OFF Delay Time	$t_{d(off)}$	∕		230		ns
Fall Time	t_f	∕		150		ns
Diode Forward Voltage	V_{SD}	$I_S = -10A, V_{GS} = 0$	- 1.0	- 1.5		V

Switching Time Test Circuit



Package Dimensions 2090A

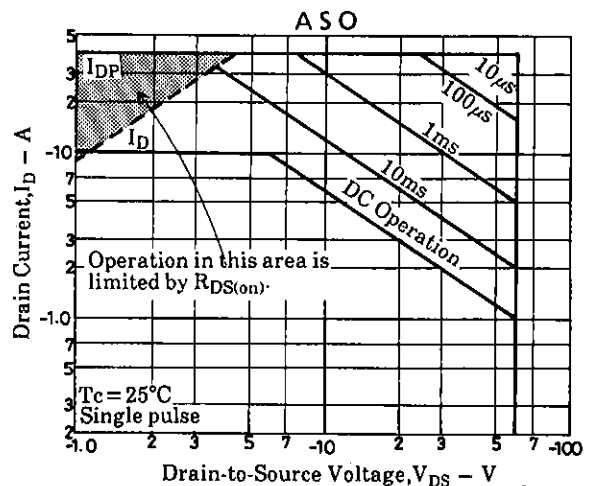
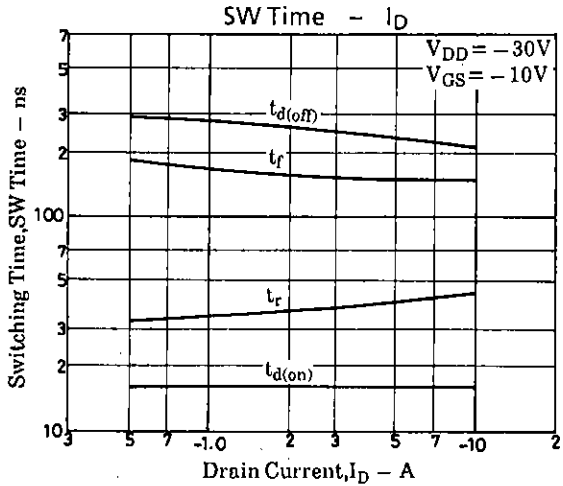
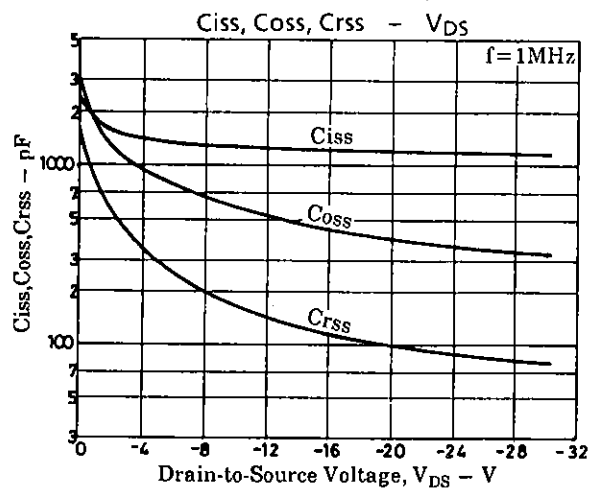
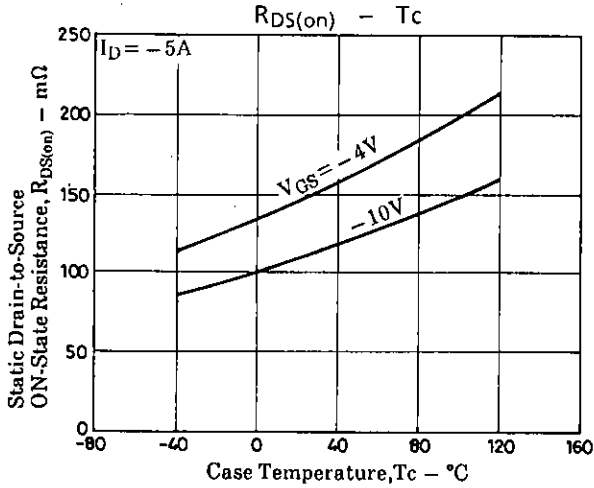
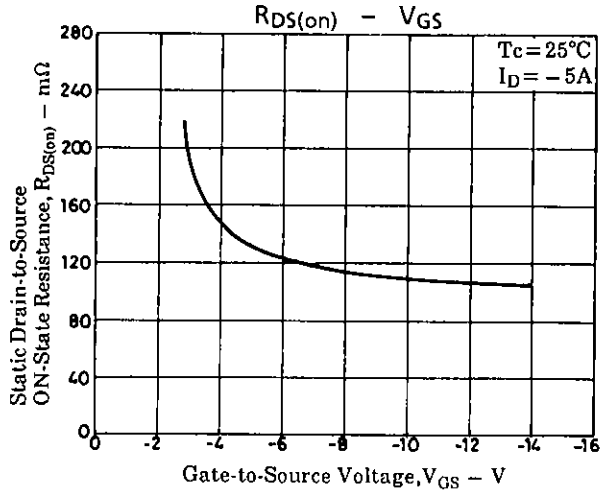
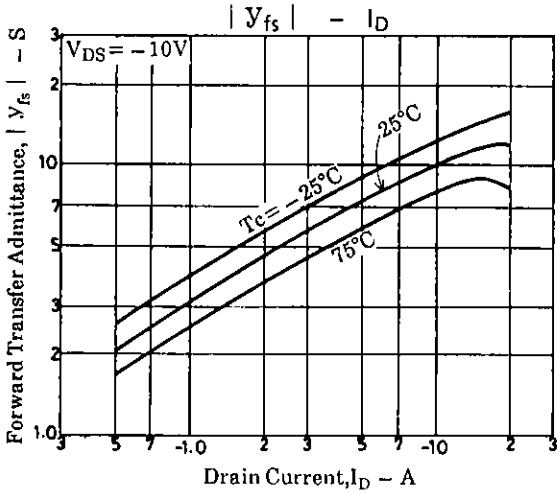
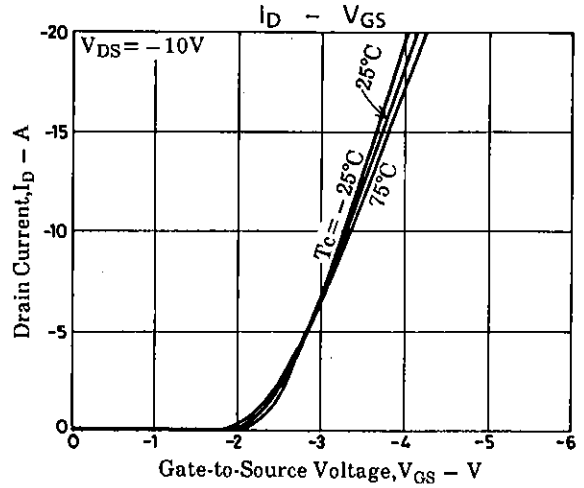
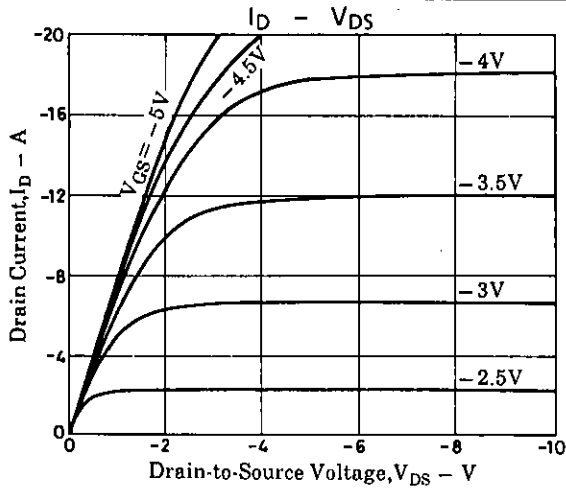
(unit : mm)

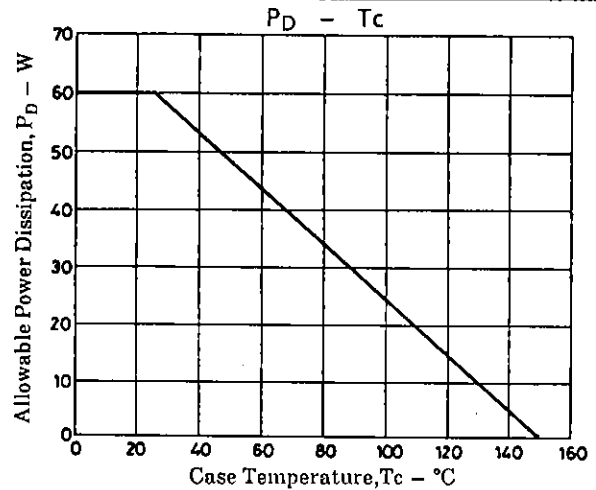
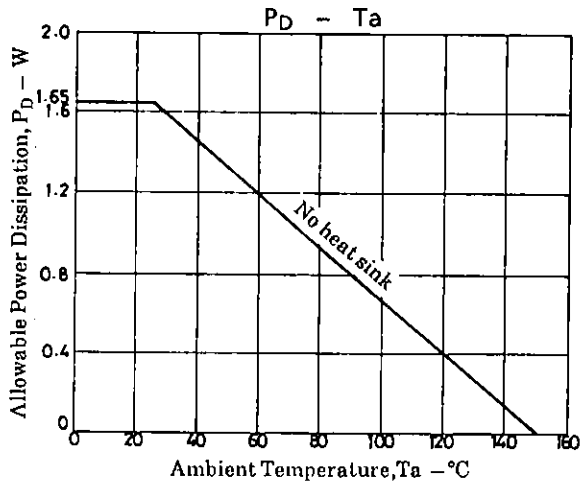


- 1: Gate
- 2: Drain
- 3: Source

SANYO: SMP-FD

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